★ Green Device Available
★ Super Low Gate Charge
★ Excellent Cdv/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

Green

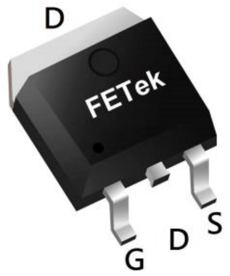
BVDSS	RDSON	ID
100V	22mΩ	40A

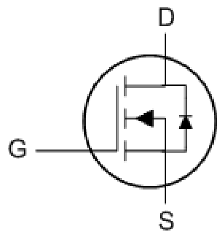
Description

The FKH0026 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FKH0026 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO263 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25˚C	Continuous Drain Current, V_{GS} @ 10V[1]	40	A
I_D@T_C=70˚C	Continuous Drain Current, V_{GS} @ 10V[1]	22	A
I_{DM}	Pulsed Drain Current[2]	75	A
EAS	Single Pulse Avalanche Energy[3]	16	mJ
I_{AS}	Avalanche Current	18	A
P_D@T_C=25˚C	Total Power Dissipation[4]	62.5	W
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	50	˚C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	2	˚C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=9A	---	16	22	mΩ
		V_{GS}=4.5V , I_D=7A	---	20	28	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=80V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=80V , V_{GS}=0V , T_J=55℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=9A	---	28	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.6	---	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=80V , V_{GS}=10V , I_D=7A	---	36	---	nC
Q_{gs}	Gate-Source Charge		---	5	---	
Q_{gd}	Gate-Drain Charge		---	10	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=50V , V_{GS}=10V , R_G=3.3Ω I_D=7A	---	11.5	---	ns
T_r	Rise Time		---	29	---	
$T_{d(off)}$	Turn-Off Delay Time		---	42	---	
T_f	Fall Time		---	18	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	1930	---	pF
C_{oss}	Output Capacitance		---	245	---	
C_{rss}	Reverse Transfer Capacitance		---	125	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	40	A
I_{SM}	Pulsed Source Current[2,6]		---	---	75	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=7A , di/dt=100A/µs , T_J=25℃	---	48	---	nS
Q_{rr}	Reverse Recovery Charge		---	29	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

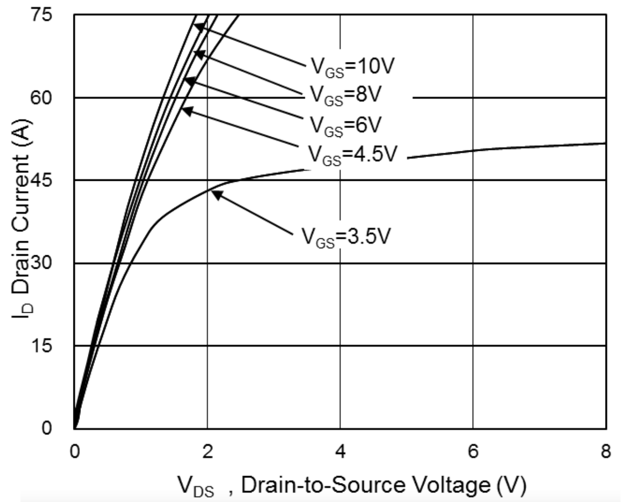


Fig.1 Typical Output Characteristics

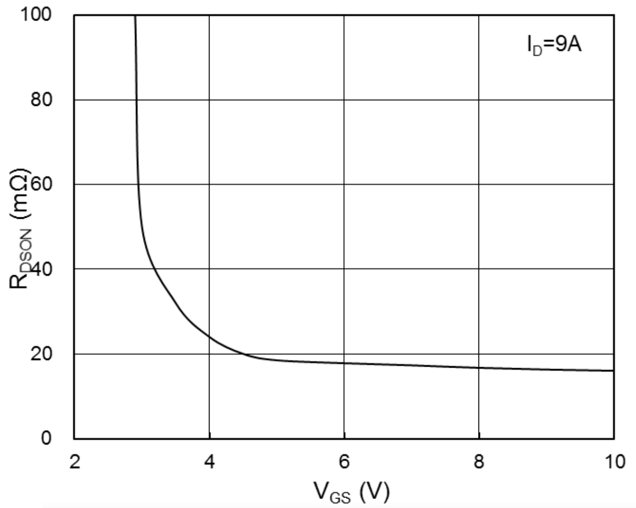


Fig.2 On-Resistance vs. Gate-Source Voltage

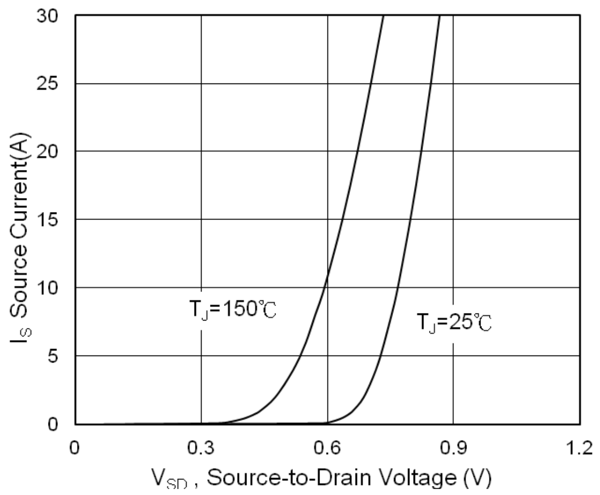


Fig.3 Forward Characteristics of Reverse

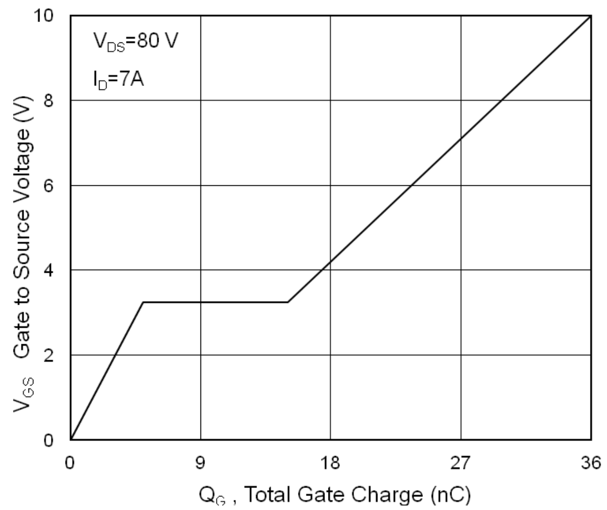


Fig.4 Gate-Charge Characteristics

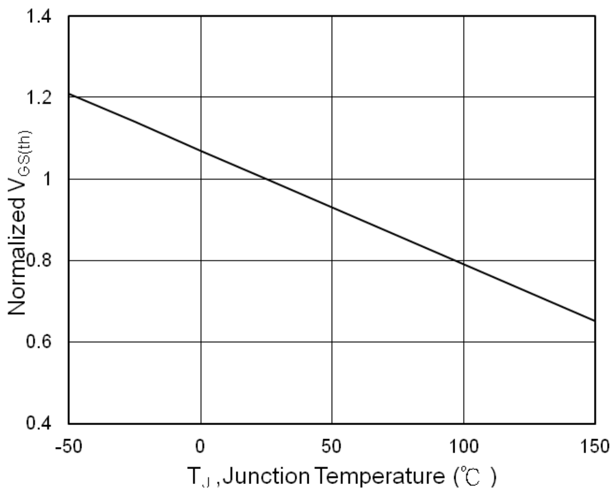


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

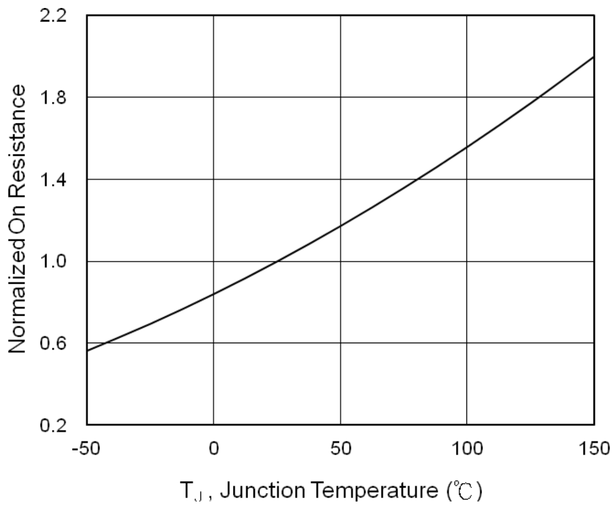


Fig.6 Normalized R_{DSON} vs. T_J

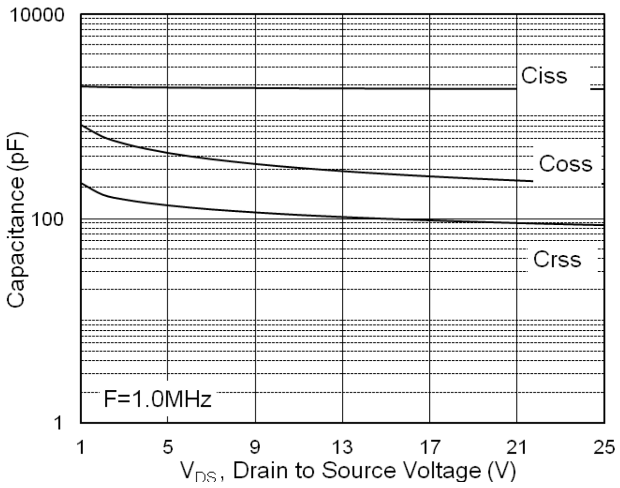


Fig.7 Capacitance

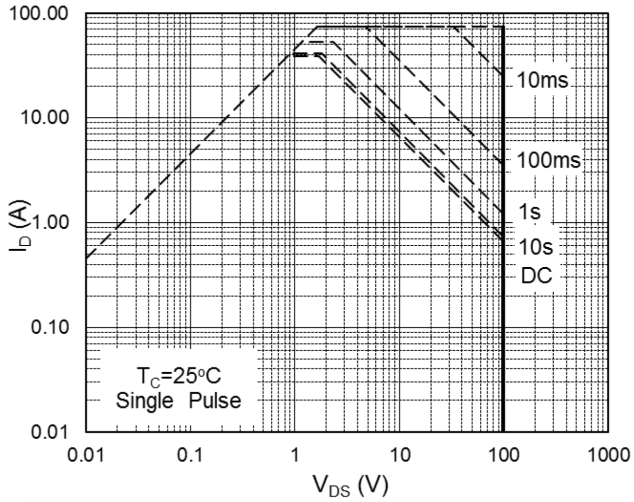


Fig.8 Safe Operating Area

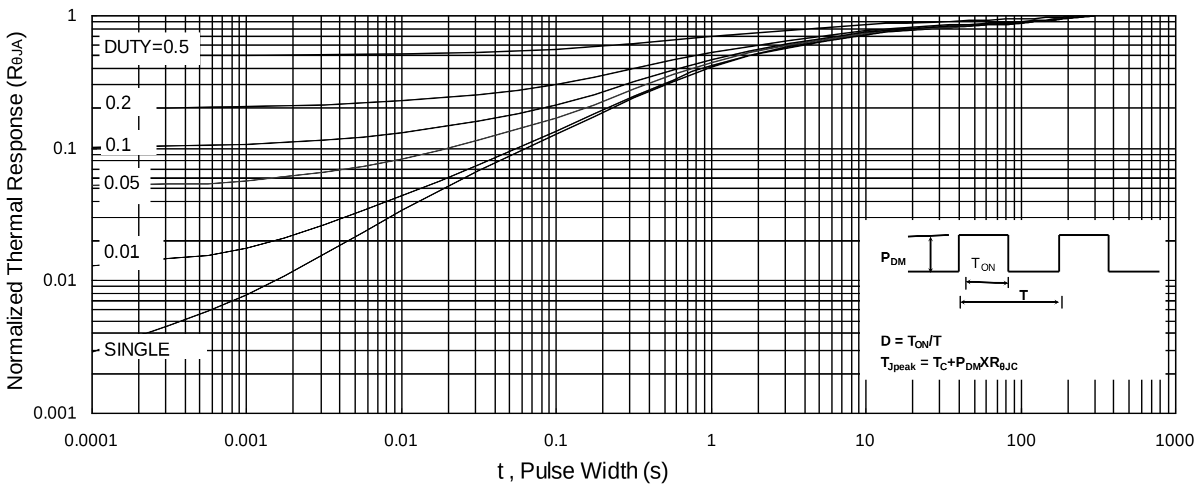


Fig.9 Normalized Maximum Transient Thermal Impedance

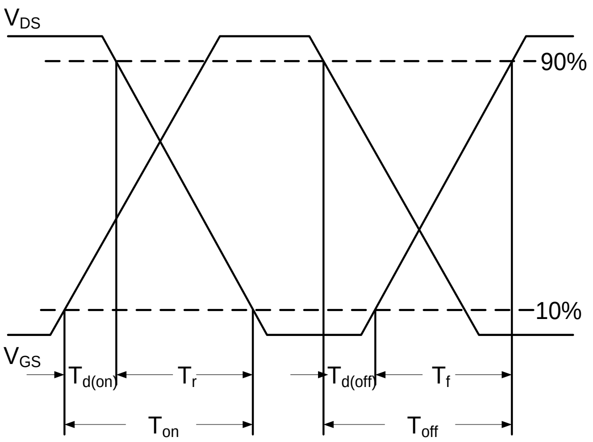


Fig.10 Switching Time Waveform

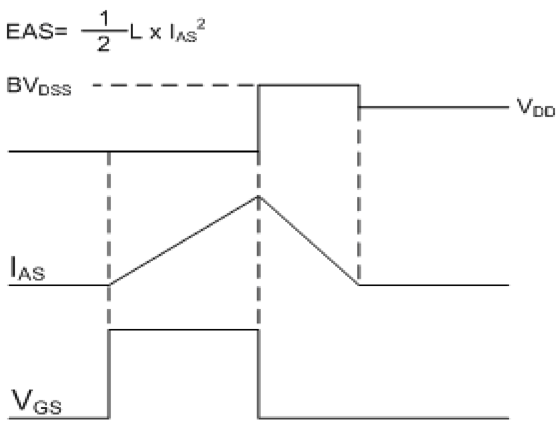
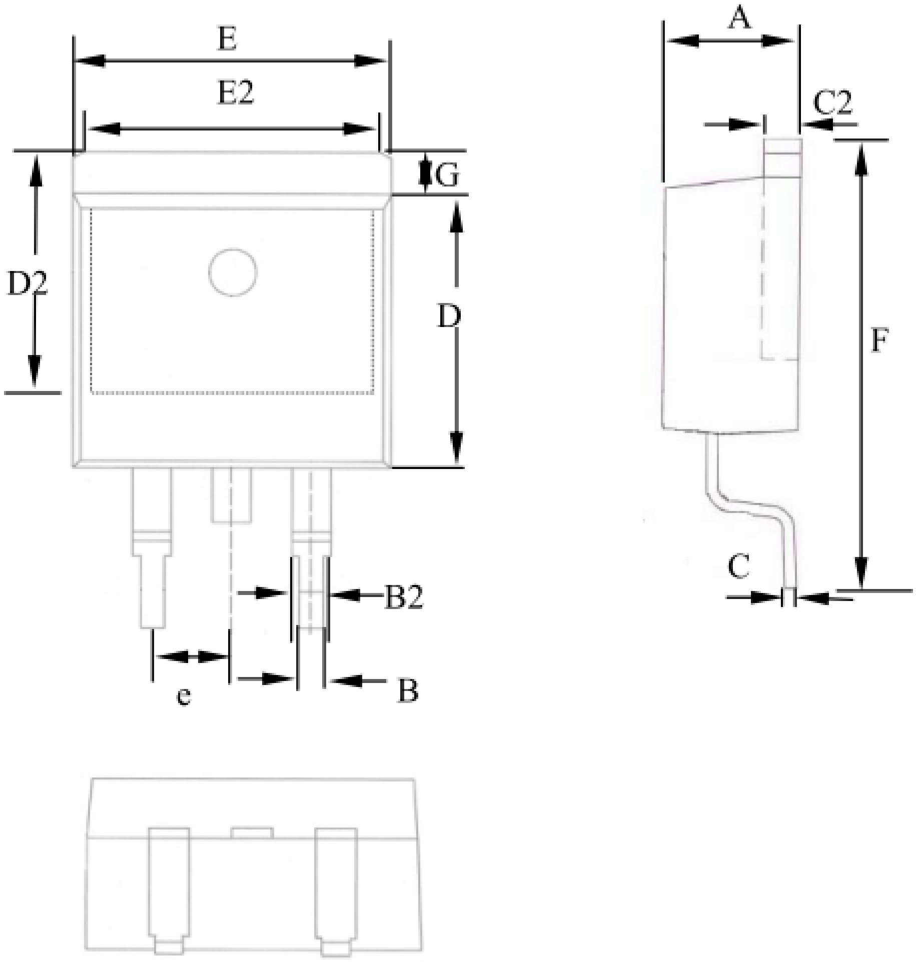


Fig.11 Unclamped Inductive Switching Waveform

TO263 Package Outline Dimensions



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM		MIN	NOM	
A	4.40	4.57	4.70	0.173	0.180	0.185
B	0.77	—	0.90	0.030	—	0.035
B2	1.23	—	1.36	0.048	—	0.054
C	0.34	—	0.47	0.013	—	0.019
C2	1.22	—	1.32	0.048	—	0.052
D	8.60	8.70	8.80	0.339	0.343	0.346
D2	7.20	7.40	7.60	0.283	0.291	0.299
E	10.06	10.16	10.26	0.396	0.400	0.404
E2	7.00	7.20	7.40	0.276	0.283	0.291
F	14.70	15.10	15.50	0.579	0.594	0.610
G	1.17	1.27	1.40	0.046	0.050	0.055
e	—	2.54	—	—	0.100	—